



PRODUCT NAME : 2SB544 PNP General Purpose Transistor

PRICE : Rs 25.00

SKU : RM2140



DESCRIPTION

Features

- Collector-Emitter Volt (V_{ce0}): 25V
- Collector-Base Volt (V_{cb0}): 25V
- Collector Current (I_c): 1.0A
- h_{fe} : 60-560 @ 50mA
- Power Dissipation (P_{tot}): 900mW
- Current-Gain-Bandwidth (f_{total}): 180MHz
- Type: PNP

Ordering number: EN 199J

SANYO	No.199J	<h2 style="margin: 0;">2SB544/2SD400</h2> <p style="margin: 0;">PNP/NPN Epitaxial Planar Silicon Transistors</p> <p style="margin: 0;">Low-Frequency Power Amp, Electronic Governor Applications</p>
--------------	---------	--

(): 2SB544

Absolute Maximum Ratings at Ta = 25°C

			unit
Collector to Base Voltage	V _{CB0}	(-)25	V
Collector to Emitter Voltage	V _{CE0}	(-)25	V
Emitter to Base Voltage	V _{EB0}	(-)5	V
Collector Current	I _C	(-)1	A
Collector Current(Pulse)	I _{CP}	(-)2	A
Collector Dissipation	P _C	900	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

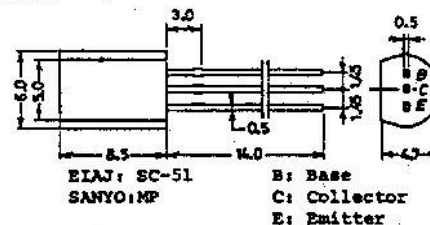
Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
Collector Cutoff Current	I _{CB0}	V _{CB} = (-)20V, I _E = 0			(-)1.0	μA
Emitter Cutoff Current	I _{EB0}	V _{EB} = (-)4V, I _C = 0			(-)1.0	μA
DC Current Gain	h _{FE} (1)	V _{CE} = (-)2V, I _C = (-)50mA	60*		560*	
	h _{FE} (2)	V _{CE} = (-)2V, I _C = (-)1A	30			
Gain-Bandwidth Product	f _T	V _{CE} = (-)10V, I _C = (-)50mA		180		MHz
Output Capacitance	c _{ob}	V _{CB} = (-)10V, f = 1MHz		(25)		pF
				15		
C-E Saturation Voltage	V _{CE(sat)}	I _C = (-)500mA, I _B = (-)50mA	(-0.15)	(-0.7)		V
			0.1	0.3		
B-E Saturation Voltage	V _{BE(sat)}	I _C = (-)500mA, I _B = (-)50mA	(-0.85)	(-1.2)		V
C-B Breakdown Voltage	V _{(BR)CBO}	I _C = (-)10μA, I _E = 0	(-)25			V
C-E Breakdown Voltage	V _{(BR)CEO}	I _C = (-)1mA, R _{BE} = ∞	(-)25			V
E-B Breakdown Voltage	V _{(BR)EBO}	I _E = (-)10μA, I _C = 0	(-)5			V

* : The 2SB544/2SD400 are classified by 50mA h_{FE} as follows :

60 D 120	100 E 200	160 F 320	280 G 560
----------	-----------	-----------	-----------

Case Outline 2006A
(unit: mm)



Specifications and information herein are subject to change without notice.

SANYO Electric Co., Ltd. Semiconductor Business Headquarters
 TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

4280MO/5157AT/D174MW,TS No.199-1/3

■ 7997076 0015716 149 ■

253

